Contents

Conference information vii

Preface xi

Contents xiii

SECTION 1. GROWTH AND CHARACTERIZATION

1.1. Growth and doping mechanisms

Surface processes in OMVPE – the frontiers
G.B. Stringfellow and J.K. Shurtleff, R.T. Lee, C.M. Fetzer, S.W. Jun 1

TEM study of the morphological and compositional instabilities of InGaAsP epitaxial structures
G. Patriarche, F. Glas, G.L.Roux, L. Largeau, A. Mereuta, A. Ougazzaden and J.L. Benchimol 12

MOVPE strain layers - growth and application
W. Strupiński, L. Dillner, J. Sass, K. Kosiel, J. Stake, M. Ingvarson and R. Jakieła 20

Fabrication of a P-stabilized GaP(001)-(2 × 1) surface at very low pressure studied by LEED, STM, AES, and RHEED
Y. Fukuda, N. Sekizawa, S. Mochizuki and N. Sanada 26

Sb-flow-rate dependence of triple-period (TP)-A-type atomic-ordering in $Ga_{0.5}In_{0.5}P$ grown by metalorganic-vapor-phase epitaxy
T. Suzuki, T. Ichihashi, K. Kurihara and K. Nishi 31

Perfect "fractal" behavior in XRD pattern of Ga(As,P) Fibonacci lattice grown by atomic layer epitaxy
H. Isshiki, J.S. Lee, Y. Aoyagi and T. Sugano 37

Impurity incorporation of unintentionally doped $Al_xGa_{1-x}As$ during MOVPE
K. Fujii, K. Kawamura and H. Gotoh 41

Incorporation mechanism of Si during delta-doping in GaAs singular and vicinal surfaces
J. Motohisa, C. Tazaki, M. Akabori and T. Fukui 47

Carbon doping for the GaAs base layer of Heterojunction Bipolar Transistors in a production scale MOVPE reactor
F. Brunner, T. Bergunde, E. Richter, P. Kurpas, M. Achouche, A. Maaßdorf, J. Würfl and M. Weyers 53

Heavily carbon-doped GaAsSb grown on InP for HBT applications
S.P. Watkins, O.J. Pitts, C. Dale, X.G. Xu, M.W. Dvorak, N. Matine and C.R. Bolognesi 59

Carbon doping of InAlAs in LP-MOVPE using CBr_4
A. Ougazzaden, J. Holavanahalli, M. Geva and L.E. Smith 66

Comparison of MOVPE-based Zn diffusion into InGaAsP/InP using H_2 and N_2 carrier gas
H. Schroeter-Janssen, H. Roehle, D. Franke, R. Bochnia, P. Harde and N. Grote 70

Influence of Zn introduction on $Al_xGa_{1-x}As$ crystal growth by MOVPE
K. Fujii, K. Kawamura and H. Gotoh 75

1.2. Precursors

Synthesis of oxygen-free trimethylindium using second generation adduct purification techniques
K.M. Coward, A.C. Jones, J.F. Bickley, A. Steiner, L.M. Smith, M.S. Ravetz, S.A. Rushworth, R. Odedra, J.S. Roberts and M.E. Pemble 81

Low oxygen content trimethylaluminium and trimethylindium for MOVPE of light emitting devices
L.M. Smith, S.A. Rushworth, M.S. Ravetz, R. Odedra, R. Kanjolia, C. Agert, F. Dimroth, U. Schubert and A.W. Bett 86

On the choice of precursors for the MOVPE-growth of high-quality $Al_{0.30}Ga_{0.70}As$/GaAs v-groove quantum wires with large subband spacing
A. Kaluza, A. Schwarz, D. Gauer, H. Hardtdegen, N. Nastase, H. Lüth, Th. Schäpers, D. Meertens, A. Maciel, J. Ryan and E. O'Sullivan 91

1.3. In situ characterization and process control

In situ studies of the effect of silicon on GaN growth modes
A. Munkholm, G.B. Stephenson, J.A. Eastman, O. Auciello, M.V. Ramana Murty, C. Thompson, P. Fini, J.S. Speck and S.P. DenBaars 98

In situ observation of superstructures on InP(0 0 1) surface under hydrogen atmospheric environment with using grazing incidence X-ray diffraction
T. Kawamura, Y. Watanabe, Y. Utsumi, K. Uwai, J. Matsui, Y. Kagoshima, Y. Tsusaka and S. Fujikawa 106

Real-time monitoring of ellipsometry monolayer oscillations during metalorganic vapor-phase epitaxy
J.-S. Lee and Y. Masumoto 111

In situ monitoring of the MOCVD growth of CdS/CdTe
S.J.C. Irvine, A. Hartley and A. Stafford 117

Reflectance anisotropy spectra for the transition from the P-rich to the In-rich surface reconstruction of InP(1 0 0)
T. Hannappel, S. Visbeck, M. Zorn, J.-T. Zettler and F. Willig 124

Kinetic study of P and As desorption from binary and ternary III–V semiconductors surface by in situ ellipsometry
O. Féron, Y. Nakano and Y. Shimogaki 129

Kinetic ellipsometry measurement of InGaP/GaAs hetero-interface formation in MOVPE
T. Nakano, Y. Nakano and Y. Shimogaki 136

Quantifying the smoothing of GaN epilayer growth by in situ laser interferometry
A. Stafford, S.J.C. Irvine, Z. Bougrioua, K. Jacobs, I. Moerman, E.J. Thrush and L. Considine 142

In situ investigation of GaAs (0 0 1) intrinsic carbon p-doping in metal-organic vapour phase epitaxy
M. Pristovsek, B. Han, J.-T. Zettler and W. Richter 149

In situ reflectance monitoring of overgrowth of InGaAs gratings in laser diode manufacture
C.W. Ebert, C.H. Joyner, G.K. Rao and R.D. Venables 156

In situ characterisation of epiready III–V substrates for MOVPE
D.A. Allwood, I.R. Grant, N.J. Mason, R.A. Palmer and P.J. Walker 160

Infrared single wavelength gas composition monitoring for metalorganic vapour-phase epitaxy
S.P. Watkins, T. Pinnington, J. Hu, P. Yeo, M. Kluth, N.J. Mason, R.J. Nicholas and P.J. Walker 166

Surface and bulk passivation of defects in GaAs/Si by RF plasma-assisted MOCVD
G. Wang, T. Ogawa, T. Soga, T. Jimbo and M. Umeno 172

MOVPE-based in situ etching of In(GaAs)P/InP using tertiarybutylchloride
P. Wolfram, W. Ebert, J. Kreissl and N. Grote 177

SECTION 2. SELECTIVE AREA EPITAXY AND GaAs ON Si

Highly selective growth of AlGaInAs assisted by CBr_4 during MOCVD growth
S. Arakawa, M. Itoh and A. Kasukawa 183

Growth pressure dependence of neighboring mask interference in densely arrayed narrow-stripe selective MOVPE for integrated photonic devices
S. Sudo, Y. Yokoyama, T. Nakazaki, K. Mori, K. Kudo, M. Yamaguchi and T. Sasaki 189

Wavelength control of arrayed waveguide by MOVPE selective area growth
T. Kihara, Y. Nitta, H. Suda, K. Miki and K. Shimomura 196

Constant growth of V-groove AlGaAs/GaAs multilayers on submicron gratings for complex optical devices
C.-S. Son, T.-G. Kim, X.-L. Wang and M. Ogura 201

Epitaxial regrowth of AlGaInP on AlGaInP grooved structure by MOVPE
T. Fukuhisa, O. Imafuji, M. Mannoh, M. Yuri and K. Itoh 208

GaAs buried growth over tungsten stripe using TEG and TMG
T. Arai, H. Tobita, Y. Miyamoto and K. Furuya 212

Growth of stress-reduced GaAs on Si substrate by using epitaxial lift-off and MOCVD regrowth
T. Soga, J. Arokiaraj, H. Taguchi, T. Jimbo and M. Umeno 220

Conformal MOVPE of (Al)GaAs on silicon using alternative chlorine-containing precursors
M. Philippens, R. Oligschlaeger, B. Gerard, S. Rushworth, E. Gil-Lafon, J. Napierala, J. Jimenez and K. Heime 225

SECTION 3. NITRIDE SEMICONDUCTORS

3.1. Growth and process control

Progress in crystal growth of nitride semiconductors
I. Akasaki 231

Time-resolved photoluminescence study of GaN grown by metalorganic chemical vapor deposition
H.K. Kwon, C.J. Eiting, D.J.H. Lambert, M.M. Wong, B.S. Shelton, T.G. Zhu, Z. Liliental-Weber, M. Benamura and R.D. Dupuis 240

MOVPE of GaN on sapphire using the alternate precursor 1,1-dimethylhydrazine
E.D. Bourret-Courchesne, K.-M. Yu, S.J.C. Irvine, A. Stafford, S.A. Rushworth, L.M. Smith and R. Kanjolia 246

Nearly strain-free AlGaN on (0001) sapphire: X-ray measurements and a new crystallographic growth model
A. Krost, J. Bläsing, F. Schulze, O. Schön, A. Alam and M. Heuken 251

Growth of AlN on sapphire substrates by using a thin AlN buffer layer grown two-dimensionally at a very low V/III ratio
Y. Ohba and R. Sato 258

In situ and ex situ evaluation of the film coalescence for GaN growth on GaN nucleation layers
S. Figge, T. Böttcher, S. Einfeldt and D. Hommel 262

High hole concentrations in Mg-doped InGaN grown by MOVPE
K. Kumakura, T. Makimoto and N. Kobayashi 267

AFM measurement of initially grown GaN layer on GaAs substrate
H. Tanaka and A. Nakadaira 271

Metalorganic vapor-phase epitaxy of cubic GaN on GaAs (100) substrates by inserting an intermediate protection layer
J. Wu, F. Zhao, K. Onabe and Y. Shiraki 276

AlAs/GaAs(001) as a template for c-oriented hexagonal GaN grown by metalorganic vapor-phase epitaxy
T. Ishido, M. Funato, A. Hamaguchi, S. Fujita and S. Fujita 280

Growth characteristics of GaN on (0 0 1) GaP substrates by MOVPE
D.-S. Wuu, W.-T. Lin, C.-C. Pan and R.-H. Horng 286

Structural investigation of GaN layers grown on Si(1 1 1) substrates using a nitridated AlAs buffer layer
A. Strittmatter, D. Bimberg, A. Krost, J. Bläsing and P. Veit 293

Nucleation control in MOVPE of group III-nitrides on SiC substrate
T. Nishida and N. Kobayashi 297

Growth and characterization of graded AlGaN conducting buffer layers on n^+ SiC substrates
B. Moran, M. Hansen, M.D. Craven, J.S. Speck and S.P. DenBaars 301

Low-temperature growth of GaN by remote-plasma-enhanced organometallic vapor-phase epitaxy
A. Wakahara, J. Genba, A. Yoshida and H. Saiki 305

Growth of GaN film on *a*-plane sapphire substrates by plasma-assisted MOCVD
Sugianto, R.A. Sani, P. Arifin, M. Budiman and M. Barmawi 311

3.2. Defect density control

Fabrication and characterization of low defect density GaN using facet-controlled epitaxial lateral overgrowth (FACELO)
K. Hiramatsu, K. Nishiyama, M. Onishi, H. Mizutani, M. Narukawa, A. Motogaito, H. Miyake, Y. Iyechika and T. Maeda 316

Control of crystalline quality of MOVPE-grown GaN and (Al,Ga)N/AlGaN MQW using In-doping and/or N_2 carrier gas
S. Yamaguchi, M. Kariya, S. Nitta, T. Kashima, M. Kosaki, Y. Yukawa, H. Amano and I. Akasaki 327

A new method of reducing dislocation density in GaN layer grown on sapphire substrate by MOVPE
S. Sakai, T. Wang, Y. Morishima and Y. Naoi 334

High-quality GaN films obtained by air-bridged lateral epitaxial growth
A. Ishibashi, I. Kidoguchi, G. Sugahara and Y. Ban 338

Drastic reduction of threading dislocation in GaN regrown on grooved stripe structure
M. Ishida, M. Ogawa, K. Orita, O. Imafuji, M. Yuri, T. Sugino and K. Itoh 345

Reduced damage of electron cyclotron resonance etching by In doping into p-GaN
T. Makimoto, K. Kumakura and N. Kobayashi 350

In situ annealing treatment and In-doping of GaN epilayers grown by MOVPE
D.-C. Lu, C. Wang, H. Yuan, X. Liu and X. Wang 356

3.3. Layered structures

Optical properties of undoped and modulation-doped $Al_xGa_{1-x}N$/GaN heterostructures grown by metalorganic chemical vapor deposition
H.K. Kwon, C.J. Eiting, D.J.H. Lambert, B.S. Shelton, M.M. Wong, T.G. Zhu and R.D. Dupuis 362

Structural and optical properties of InGaN/GaN multiple quantum wells: The effect of the number of InGaN/GaN pairs
D.-J. Kim, Y.-T. Moon, K.-M. Song, C.-J. Choi, Y.-W. Ok, T.-Y. Seong and S.-J. Park 368

MOCVD growth, stimulated emission and time-resolved PL studies of InGaN/(In)GaN MQWs: well and barrier thickness dependence
S. Shee, Y.H. Kwon, J.B. Lam, G.H. Gainer, G.H. Park, S.J. Hwang, B.D. Little and J.J. Song 373

Growth of BGaN/AlGaN multi-quantum-well structure by metalorganic vapor phase epitaxy
M. Kurimoto, T. Takano, J. Yamamoto, Y. Ishihara, M. Horie, M. Tsubamoto and H. Kawanishi 378

SECTION 4. II–VI SEMICONDUCTORS AND OXIDES

The reaction mechanisms for precursors in photo-assisted metalorganic-vapor-phase epitaxy growth of ZnSe
Y. Fujita 382

Optical and structural properties of high-quality ZnS epitaxial layers grown on GaAs substrates by low-pressure metalorganic chemical vapor deposition
S. Nakamura, S. Takagimoto, T. Ando, H. Kugimiya, Y. Yamada and T. Taguchi 388

Compensation of nitrogen acceptor in ZnSe:N/ZnSe grown by MOCVD
J. Wang, T. Miki, A. Omino, K.S. Park and M. Isshiki 393

Deep levels in Sb-doped ZnSe fabricated by metalorganic vapor-phase epitaxy
T. Kawahara, Y. Ohbuchi, N. Tabuchi, J. Morimoto, H. Goto and T. Ido 398

Effects of substrate temperature upon photoluminescence properties of ZnTe layers grown by photo-assisted MOVPE
K. Hayashida, M. Nishio, H. Harada, S. Furukawa, Q. Guo and H. Ogawa 404

Low pressure MOVPE growth and structural properties of ZnMgSe epilayers on (1 0 0)GaAs
P. Prete, N. Lovergine, L. Tapfer, M. Berti, S.K. Sinha and A.M. Mancini 410

ZnMgCdSe structures on InP grown by MOVPE
M. Straßburg, M. Straßburg, O. Schulz, U.W. Pohl, D. Bimberg, D. Litvinov, D. Gerthsen, M. Schmidbauer and P. Schäfer 416

Epitaxial growth of $Mg_xZn_{1-x}S$ heterostructures by low-pressure MOCVD
K. Yoshimura, S. Ishizaki, Y. Yamada and T. Taguchi 421

Growth mechanism of selectively grown II–VI semiconductor photonic dots for short-wavelength light emitters
A. Ueta, T. Shimozawa, A. Avramescu, I. Suemune, H. Machida and N. Shimoyama 425

Hetero-epitaxial growth of ZnO thin films by atmospheric pressure CVD method
Y. Kashiwaba, F. Katahira, K. Haga, T. Sekiguchi and H. Watanabe 431

Role of ZnS buffer layers in growth of zincblende ZnO on GaAs substrates by metalorganic molecular-beam epitaxy
A.A. Ashrafi, A. Ueta, H. Kumano and I. Suemune 435

Homoepitaxial $YBa_2Cu_3O_x$ films grown on single-crystal $YBa_2Cu_3O_x$ substrates by metalorganic chemical vapor deposition using β-diketonates
H. Zama, N. Tanaka and T. Morishita 440

SECTION 5. INFRARED MATERIALS

Novel Sb-based materials for uncooled infrared photodetector applications
J.J. Lee and M. Razeghi 444

MOVPE of AlGaAsSb using TTBAl as an alternative aluminum precursor
Ch. Giesen, A. Szymakowski, S. Rushworth, M. Heuken and K. Heime 450

High nitrogen composition GaAsN by atmospheric pressure metalorganic vapor-phase epitaxy
J. Toivonen, T. Hakkarainen, M. Sopanen and H. Lipsanen 456

Observation of compositional fluctuations in GaNAs alloys grown by metalorganic vapor-phase epitaxy
M. Takahashi, A. Moto, S. Tanaka, T. Tanabe, S. Takagishi, K. Karatani, M. Nakayama, K. Matsuda and T. Saiki 461

Spatial distribution of deep level traps in GaNAs crystals
S. Tanaka, A. Moto, M. Takahashi, T. Tanabe and S. Takagishi 467

AFM study and optical properties of GaAsN/GaAs epilayers grown by MOVPE
L. Auvray, H. Dumont, J. Dazord, Y. Monteil, J. Bouix and C. Bru-Chevalier 475

Optical characterization of metalorganic vapor-phase epitaxy-grown $GaAs_{1-x}N_x$ alloys using spectroscopic ellipsometry
S. Matsumoto, H. Yaguchi, S. Kashiwase, T. Hashimoto, S. Yoshida, D. Aoki and K. Onabe 481

Hydrogen and carbon incorporation in GaInNAs
A. Moto, M. Takahashi and S. Takagishi 485

Effects of thermal annealing procedure and a strained intermediate layer on a highly-strained GaInNAs/GaAs double-quantum-well structure
T. Kitatani, M. Kondow and T. Tanaka 491

Effect of growth conditions and strain compensation on indium incorporation for diode lasers emitting above 1050 nm
F. Bugge, U. Zeimer, S. Gramlich, I. Rechenberg, J. Sebastian, G. Erbert and M. Weyers 496

Critical layer thickness of 1.2-μm highly strained GaInAs/GaAs quantum wells
D. Schlenker, T. Miyamoto, Z.B. Chen, M. Kawaguchi, T. Kondo, E. Gouardes, F. Koyama and K. Iga 503

SECTION 6. LOW DIMENSIONAL STRUCTURES

6.1. Quantum wells

Characterization of InGaP/GaAs heterointerfaces grown by metal organic vapour phase epitaxy
T.K. Sharma, B.M. Arora, M.R. Gokhale and S. Rajgopalan 509

Ordering-induced electron accumulation at GaInP/GaAs hetero-interfaces
T. Tanaka, K. Takano, T. Tsuchiya and H. Sakaguchi 515

Rapid high-resolution X-ray diffraction measurement and analysis of MOVPE pHEMT structures using a high-brilliance X-ray source and automatic pattern fitting
T. Lafford, M. Taylor, J. Wall and N. Loxley 520

MOVPE growth and properties of P-I-N InGaAs/GaAs strained multi-quantum well structures on (1 1 1)A GaAs substrates
J. Kim, S. Cho, A. Sanz-Hervás, A. Majerfeld and B.W. Kim 525

Growth and optical properties of highly strained GaInAs/GaAs quantum wells on (3 1 1)B GaAs by MOCVD
N. Nishiyama, M. Arai, S. Shinada, T. Miyamoto, F. Koyama and K. Iga 530

Influence of compressive strain on the arsenic incorporation in MOVPE-grown InAsP/InP single quantum wells
R. Venkataraghavan, M.R. Gokhale, A.P. Shah, A. Bhattacharya, K.S. Chandrasekaran and B.M. Arora 535

6.2. Quantum wires

OMVPE fabrication of continuous transitions between GaAs/AlGaAs quantum wells and V-groove quantum wires
F. Lelarge, D. Kaufman, B. Dwir, S. Mautino, A. Rudra and E. Kapon 540

Formation of wire-like surfaces and lateral composition modulation in GaAsN grown by metalorganic molecular-beam epitaxy
I. Suemune, N. Morooka, K. Uesugi, Y.-W. Ok and T.-Y. Seong 546

Origin of disorder in self-ordered GaAs/AlGaAs quantum wires grown by OMVPE on V-grooved substrate
F. Lelarge, T. Otterburg, D.Y. Oberli, A. Rudra and E. Kapon 551

Flow rate modulation epitaxy of high-quality V-shaped AlGaAs/GaAs quantum wires using tertiarybutylarsine as the arsenic source
X.-L. Wang and M. Ogura 556

6.3. Quantum dots

GaInNAs/GaAs quantum dots grown by chemical beam epitaxy
S. Makino, T. Miyamoto, T. Kageyama, N. Nishiyama, F. Koyama and K. Iga 561

Size control of self-assembled quantum dots
J. Johansson and W. Seifert 566

Growth of self-assembled $Ga_xIn_{1-x}P$ quantum islands on GaP
J. Porsche and F. Scholz 571

Formation of uniform 10-nm-scale InGaN quantum dots by selective MOCVD growth and their micro-photoluminescence intensity images
K. Tachibana, T. Someya, S. Ishida and Y. Arakawa 576

Surface flattening during MOCVD of thin GaAs layers covering InGaAs quantum dots
R. Sellin, F. Heinrichsdorff, Ch. Ribbat, M. Grundmann, U.W. Pohl and D. Bimberg 581

Low-index facet formation in InGaAs islands on GaAs (*n*11)B substrates
J.-S. Lee, K. Nishi and Y. Masumoto 586

Optimizing the growth procedure for InAs quantum dot stacks by optical in situ techniques
E. Steimetz, T. Wehnert, H. Kirmse, F. Poser, J.-T. Zettler, W. Neumann and W. Richter 592

Position and number control of self-assembled InAs quantum dots by selective area metalorganic vapor-phase epitaxy
C.K. Hahn, J. Motohisa and T. Fukui 599

Magnetic and optical properties of Mn-including InAs dots grown by metalorganic molecular beam epitaxy
Y.K. Zhou, H. Asahi, J. Asakura, S. Okumura, K. Asami and S. Gonda 605

Thin GaSb insertions and quantum dot formation in GaAs by MOCVD
L. Müller-Kirsch, U.W. Pohl, R. Heitz, H. Kirmse, W. Neumann and D. Bimberg 611

SECTION 7. GROWTH SYSTEM

Performance of multiwafer reactor GaN MOCVD system
H. Tokunaga, H. Tan, Y. Inaishi, T. Arai, A. Yamaguchi and J. Hidaka 616

Fundamental models of the metalorganic vapor-phase epitaxy of gallium nitride and their use in reactor design
R.P. Pawlowski, C. Theodoropoulos, A.G. Salinger, T.J. Mountziaris, H.K. Moffat, J.N. Shadid and E.J. Thrush 622

Uniformity control of group-III nitrides grown on 5×3 inch Al_2O_3 substrates in Planetary Reactors®
H. Protzmann, M. Luenenbuerger, M. Bremser, M. Heuken and H. Juergensen 629

A study of cylinder design for solid OMVPE sources
M. Timmons, P. Rangarajan and R. Stennick 635

SECTION 8. DEVICE STRUCTURES

8.1. Optoelectronic devices

Properties of GaN-based laser diodes with a buried-ridge structure
T. Asatsuma, H. Nakajima, S. Hashimoto, T. Yamaguchi, H. Yoshida, S. Tomiya, T. Asano, T. Hino, M. Ozawa, T. Miyajima, T. Kobayashi and M. Ikeda 640

AlGaInN high-power lasers grown on an ELO-GaN layer
M. Takeya, K. Yanashima, T. Asano, T. Hino, S. Ikeda, K. Shibuya, S. Kijima, T. Tojyo, S. Ansai, S. Uchida, Y. Yabuki, T. Aoki, T. Asatsuma, M. Ozawa, T. Kobayashi, E. Morita and M. Ikeda 646

High-power ohmic-electrodes dispersive AlGaInP double-hetero structure yellowish-green light-emitting diodes
Y. Hosokawa, W. Nabekura, T. Hoshina, R. Takeuchi, K. Sakaue and T. Udagawa 652

Low threshold current densities in red VCSELs
R. Butendeich, D. Graef, J. Schwarz, T. Ballmann, H. Schweizer and F. Scholz 657

Optimization of MOVPE growth for 650 nm-emitting VCSELs
A. Bhattacharya, M. Zorn, A. Oster, M. Nasarek, H. Wenzel, J. Sebastian, M. Weyers and G. Tränkle 663

InAlGaP microcavity LEDs on Ge-substrates
P. Modak, D. Delbeke, I. Moerman, R. Baets, P. Van Daele and P. Demeester 668

InP 1.3 μm microcavity LEDs with high quantum efficiency
B. Depreter, I. Moerman, R. Baets, P. Van Daele and P. Demeester 674

High-power electrically injected mid-infrared interband lasers grown by LP-MOCVD
B. Lane and M. Razeghi 679

MOVPE growth of lattice-mismatched $Al_{0.88}In_{0.12}As$ on GaAs (1 0 0) for space solar cell applications
S. Sinharoy, M.A. Stan, A.M. Pal, V.G. Weizer, M.A. Smith, D.M. Wilt and K. Reinhardt 683

Low-temperature growth of GaAs polycrystalline films on glass substrates for space solar cell application
M. Imaizumi, M. Adachi, Y. Fujii, Y. Hayashi, T. Soga, T. Jimbo and M. Umeno 688

Polarization-insensitive InGaAsP/InP vertical coupler filter with deep grating by five-step MOVPE growth
M. Horita, T. Yazaki, S. Tanaka and Y. Matsushima 693

Microcavities with distributed Bragg reflectors based on ZnSe/MgS superlattice grown by MOVPE
T. Tawara, H. Yoshida, T. Yogo, S. Tanaka and I. Suemune 699

8.2. Electronic devices

MOVPE overgrowth of metallic features for realisation of 3D metal–semiconductor quantum devices
L.-E. Wernersson, M. Borgström, B. Gustafson, A. Gustafsson, L. Jarlskog, J.-O. Malm, A. Litwin, L. Samuelson and W. Seifert 704

Metal-organic VPE growth of electron mobility enhanced GaInP/GaInAs pseudomorphic two-dimensional FET structure
M. Kimura, T. Okano, M. Okuyama, T. Udagawa, H. Azuhata, A. Sawada and T. Takamasu 713

Low tensile strain GaInAs:uid/GaAs:C superlattice heterostructures grown by LP MOCVD: application to GaInP/GaAs heterojunction bipolar transistor base layer
M.-A. di Forte-Poisson, S. Bernard, L. Teisseire, C. Brylinski, S. Cassette and J. di Persio 717

InAlAs/InGaAs/InP heterostructures for RTD and HBT device applications grown by LP-MOVPE using non-gaseous sources
P. Velling, M. Agethen, W. Prost and F.J. Tegude 722

The growth of AlGaN/GaN heterojunction bipolar transistors by metalorganic chemical vapor deposition
D.J.H. Lambert, J.J. Huang, B.S. Shelton, M.M. Wong, U. Chowdhury, T.G. Zhu, H.K. Kwon, Z. Liliental-Weber, M. Benarama, M. Feng and R.D. Dupuis 730

Electrical transport properties of highly Mg-doped GaN epilayers grown by MOCVD
M.G. Cheong, K.S. Kim, N.W. Namgung, M.S. Han, G.M. Yang, C.-H. Hong, E.-K. Suh, K.Y. Lim, H.J. Lee and A. Yoshikawa 734

Large electron field emission from high-quality heavily Si-doped AlN grown by MOVPE
M. Kasu and N. Kobayashi 739

SECTION 9. MODELING

Thermodynamic analysis of the MOVPE growth of InGaAlN quaternary alloy
A. Koukitu, Y. Kumagai and H. Seki 743

Gas-phase chemistry of metalorganic and nitrogen-bearing compounds
R.M. Watwe, J.A. Dumesic and T.F. Kuech 751

Detailed thermal boundary conditions in the 3D fluid-dynamic modelling of horizontal MOVPE reactors
R. Mucciato and N. Lovergine 758

Regional density functional theory for crystal growth in GaN
K. Nakamura, T. Hayashi, A. Tachibana and K. Matsumoto 765

Author index to volume 221 772

Subject index to volume 221 783